



Ruttonsha International Rectifier Ltd.

HIGH POWER THYRISTOR

INVERTER GRADE THYRISTOR

Hockey Puk Version K-PUK SERIES 1125PK

Type : 1125 PK140 F To 1125 PK 200 F

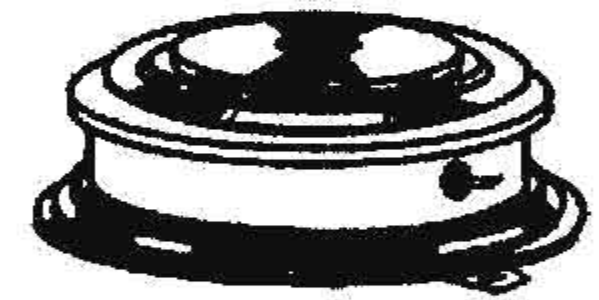
Features

- Low Switching loss at high frequency.
- 60 μ s maximum turn-off time with feedback diode.
- Involute, interdigitate gate

Typical Applications

- Inverters
- Choppers
- Induction heating
- All type of forced-Commutated converters

1125A



Case Style A- 24 (K-PUK)

Major Ratings and Characteristics :-

PARAMETERS	1125PK...F	UNITS
$I_{T(AV)}$	1125	A
@ T_{hs}	65	$^{\circ}$ C
$I_{T(RMS)}$	1766	A
@ T_{hs}	65	$^{\circ}$ C
I_{TSM}	20,000	A
I^2t	1,660	KA ² s
V_{DRM} / V_{RRM}	1400 to 2000	V
T_q typical	30 to 50	μ s
T_J	125	$^{\circ}$ C

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Electrical Specifications

Voltage Ratings

Type Number	Voltage Code	V_{DRM}/V_{RRM} , max repetitive peak voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. mA	
				25 ⁰ c	125 ⁰ c
	140	1400	1500	60	60
1125PK...F	160	1600	1700	60	60
	180	1800	1900	60	60
	200	2000	2100	60	60

On-state Conduction

	Parameter	1125PK...F	Units	Conditions
$I_{T(AV)}$	Max. average on-state current	1125	A	180° conduction, half sine wave
	@ Heatsink temperature	65	°C	double side cooled
$I_{T(RMS)}$	Max RMS on-state current	1766	A	DC @ 65 °C heatsink temperature double side cooled
V_{TM}	Max. on-state voltage	2.1	V	$I_T=1000A$, $T_J=T_J$ max., Duty Cycle $\leq 0.01\%$

Switching

	Parameter	1125PK...F	Units	Conditions
di/dt	Max. Repetitive rate of rise of turned-on current	100	A/ μ s	$T_J=T_J$ max., $V_{DRM} = \text{rated } V_{DRM}$
t_d	Typical delay time	1.5	μ s	Switching from 140V, 20V, 10 ohm Gate 0.5 μ s rise time, $T_J = 25$ °C
t_q	Typical turn-off time	30 to 50	μ s	$T_J=T_J$ max., $I_T = 1000A$, $V_R = 50V$, di/dt=25A/us 80 % V_{DRM} Reapplied, dv/dt = 400 V / μ s, Gate bias = open During Turn-Off, Interval = 0V, 100 ohm, Duty Cycle $\leq 0.01\%$

Parameter	1125PK...F	Units	Conditions
V_{TO} Threshold Voltage	1.54	V	$T_J=T_J$ max.
r_T Slope resistance	0.258	m Ω	$T_J=T_J$ max.,

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Triggering

Parameter	1125PK...F	Units	Conditions
P_{GM} Maximum peak gate power	100	W	$T_J = T_{Jmax.}$, $t_p \leq 5$ ms
$P_{G(AV)}$ Maximum average gate power	5	W	$T_J = T_{Jmax.}$, $f = 60$ Hz,
I_{GT} Max. DC gate current required to trigger	200	mA	$T_J = 25^\circ\text{C}$, $V_D = 10$ V dc $R_L = 3$ ohm
V_{GT} Max. DC gate voltage required to trigger	3.0	V	$T_J = 25^\circ\text{C}$, $V_D = 10$ V dc $R_L = 3$ ohm

Blocking

Parameter	1125PK...F	Units	Conditions
dv/dt Min. critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_{Jmax.}$ linear to 80% rated V_{DRM}
I_{RRM} Max. peak reverse and off-state leakage current	60	mA	$T_J = T_{Jmax.}$, rated V_{DRM}/V_{RRM} applied

Thermal and Mechanical Specifications

Parameter	1125PK...F	Units	Conditions
T_J Max. operating temperature	125	$^\circ\text{C}$	
T_{stg} Max. storage temperature range	- 40 to +125	$^\circ\text{C}$	
R_{thJ-hs} Max. thermal resistance, junction to heat sink	0.023	$^\circ\text{C/W}$	DC operation double side cooled
F Mounting force, $\pm 10\%$	24.5 (2500)	KN (Kg.)	
Case style	A-24 (K-PUK)		

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OUTLINE DRAWING

SUGGESTED MOUNTING METHODS FOR PRESS-PAKS TO HEAT DISSIPATORS

To achieve a reliable and low thermal resistance interface when the press pak is assembled to a heat sink the following general instructions should be followed.

1. Check each mating surface for nicks, scratches, flatness and surface finish. The heat dissipator mating surfaces should be flat with .0005 inches and have a surface finish of 63 micro-inches.
2. It is recommended that the heat dissipator be plated with nickel or tin. Bare aluminum or copper surfaces will oxidize in time resulting in excessively high thermal resistance.
3. Sand each surface lightly with 600 grit paper just prior to assembly. Clean off and apply silicone grease (GE G623 or Dow Corning DC3, 4, 340 or 640). Clean off and apply again as a thin film. (A thick film will adversely affect the electrical and thermal resistances).
4. Assemble with the specified mounting force applied through a self-leveling, swivel connection. The force has to be evenly distributed over the full area. Center holes on both top and bottom of the press-pak are for locating purposes only.

